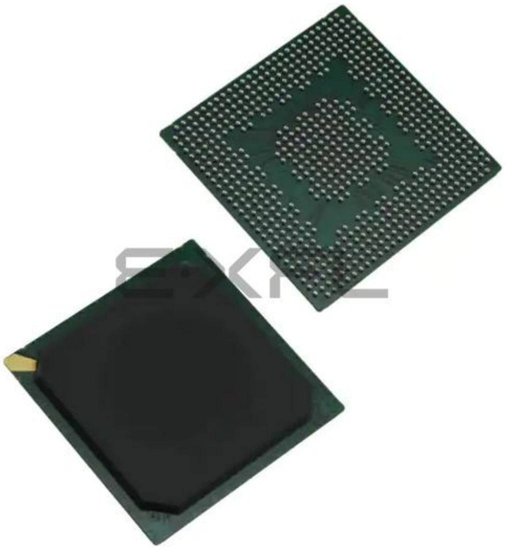

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8343vragd

Table 1. Absolute Maximum Ratings[1] (continued)

Parameter		Symbol	Max Value	Unit	Notes
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1 Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.

2 **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

3 **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

4 **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

5 (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

6 OVIN on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the MPC8343EA. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

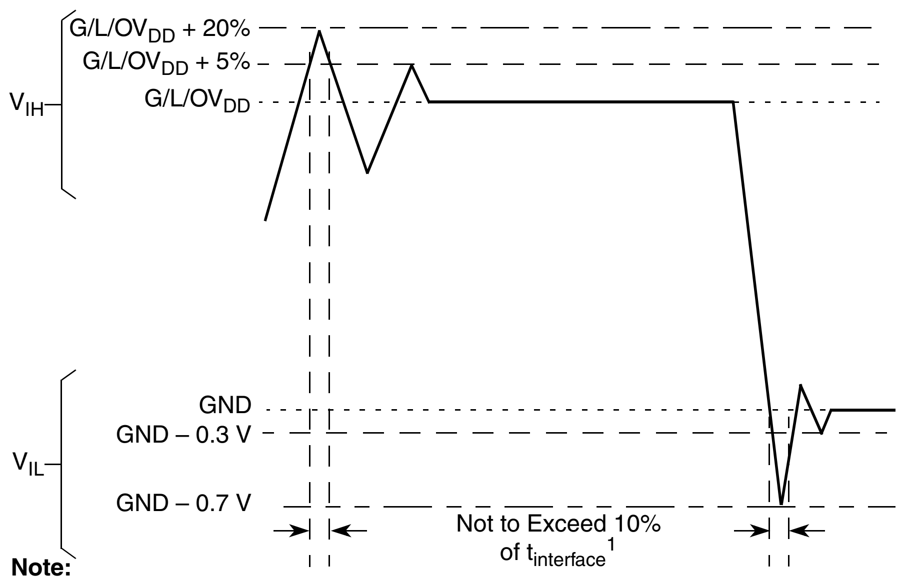
Parameter	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.2 V ± 60 mV	V	1
PLL supply voltage	AV_{DD}	1.2 V ± 60 mV	V	1
DDR and DDR2 DRAM I/O voltage	GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O supply voltage	LV_{DD1}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	LV_{DD2}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—

Table 2. Recommended Operating Conditions (continued)

Parameter	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	—

Note:
[1] GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8343EA.



Note:
1. $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

Table 5 shows the estimated typical I/O power dissipation for MPC8343EA.

Table 5. MPC8343EA Typical I/O Power Dissipation

Interface	Parameter	DDR2 GV_{DD} (1.8 V)	DDR1 GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	0.31	0.42	—	—	—	W	—
	266 MHz, 32 bits	0.35	0.5	—	—	—	W	—
PCI I/O load = 30 pF	33 MHz, 32 bits	—	—	0.04	—	—	W	—
	66 MHz, 32 bits	—	—	0.07	—	—	W	—
Local bus I/O load = 25 pF	167 MHz, 32 bits	—	—	0.34	—	—	W	—
	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—		0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—		0.06	—	W	
	RGMII or RTBI	—	—		—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	—
	480 MHz	—	—	0.2	—	—	W	—
Other I/O		—	—	0.01	—	—	W	—

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the device.

4.1 DC Electrical Characteristics

Table 6 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the MPC8343EA.

Table 6. CLKIN DC Timing Specifications

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
CLKIN input current	$0\ V \le V_{IN} \le OV_{DD}$	I_{IN}	—	±10	μA

Table 6. CLKIN DC Timing Specifications (continued)

Parameter	Condition	Symbol	Min	Max	Unit
PCI_SYNC_IN input current	0 V $\le V_{IN} \le$ 0.5 V or OV_{DD} – 0.5 V $\le V_{IN} \le OV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	0.5 V $\le V_{IN} \le OV_{DD}$ – 0.5 V	I_{IN}	—	±50	μA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8343EA can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 7 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the device.

Table 7. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66	MHz	1, 6
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:
1. **Caution:** The system, core, USB, security, and TSEC must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be < 500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.
6. Spread spectrum clocking is allowed with 1% input frequency down-spread at maximum 50 KHz modulation rate regardless of input frequency.

4.3 TSEC Gigabit Reference Clock Timing

Table 8 provides the TSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications.

Table 8. EC_GTX_CLK125 AC Timing Specifications

At recommended operating conditions with LV_{DD} = 2.5 ± 0.125 mV/ 3.3 V ± 165 mV

Parameter	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	t_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK125 rise and fall time LV_{DD} = 2.5 V LV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1

Table 13 provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR SDRAM component(s) when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 15 provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
266 MHz		–750	750		—
200 MHz		–750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: t_{DISKEW} = ± (T/4 – abs (t_{CISKEW})); where T is the clock period and abs (t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

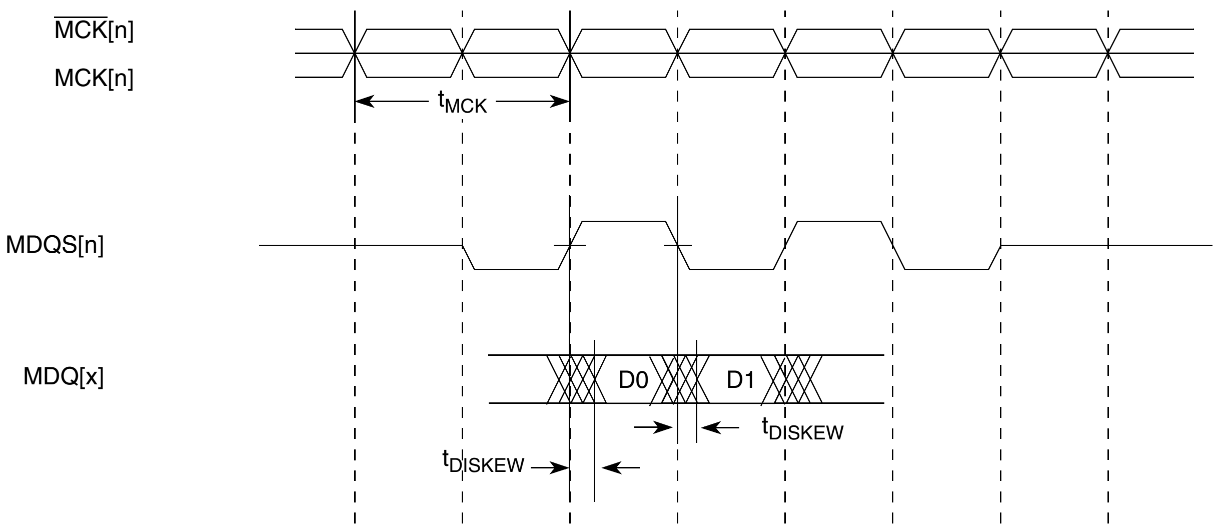


Figure 5. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{\text{MCK}}$[n] crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD/MODT output setup with respect to MCK	t_{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		

Figure 7 shows the DDR SDRAM output timing diagram.

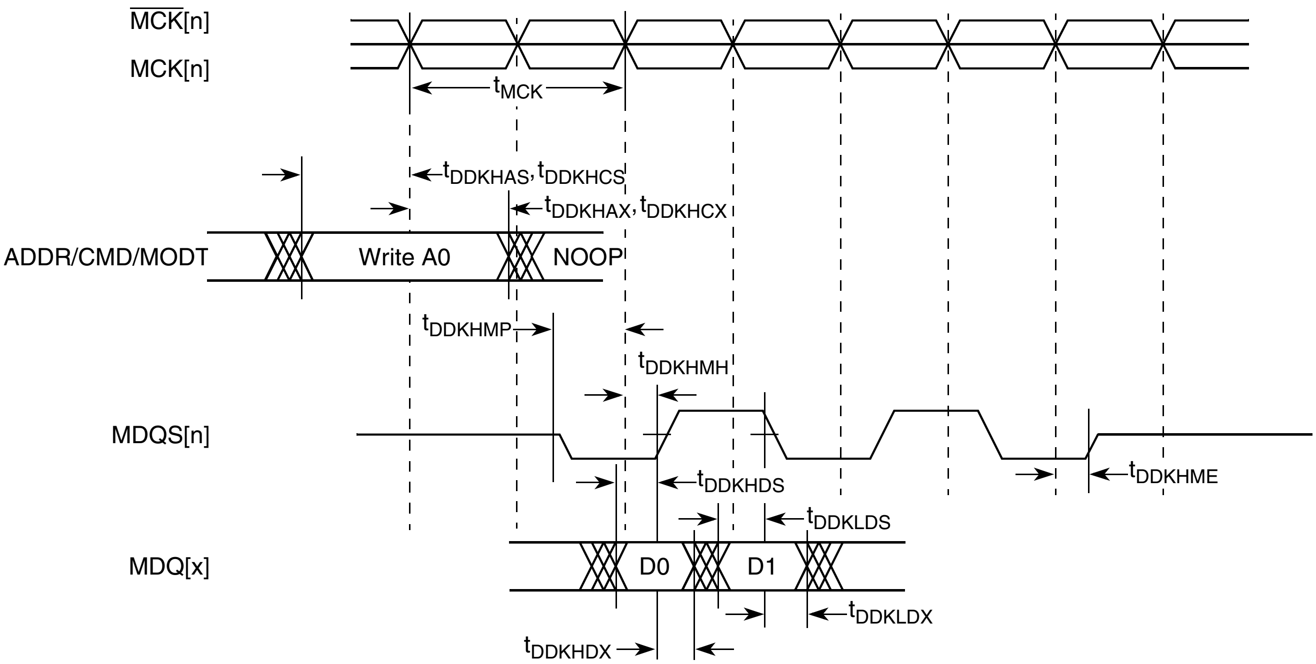


Figure 7. DDR SDRAM Output Timing Diagram

Figure 8 provides the AC test load for the DDR bus.

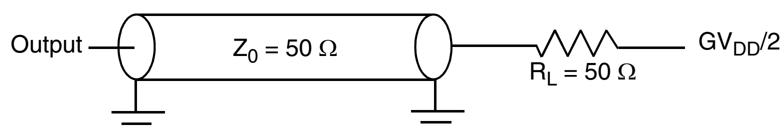


Figure 8. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8343EA.

7.1 DUART DC Electrical Characteristics

Table 21 provides the DC electrical characteristics for the DUART interface of the MPC8343EA.

Table 21. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (0.8 V ≤ V_{IN} ≤ 2 V)	I_{IN}	—	±5	μA

8.2.1.2 MII Receive AC Timing Specifications

Table 26 provides the MII receive AC timing specifications.

Table 26. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise (20%–80%)	t_{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time (80%–20%)	t_{MRXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 provides the AC test load for TSEC.

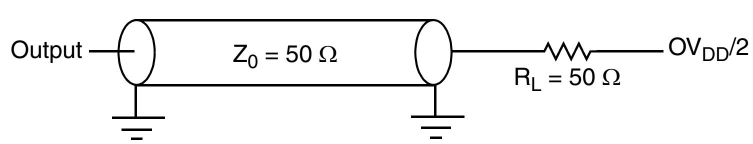


Figure 10. TSEC AC Test Load

Figure 11 shows the MII receive AC timing diagram.

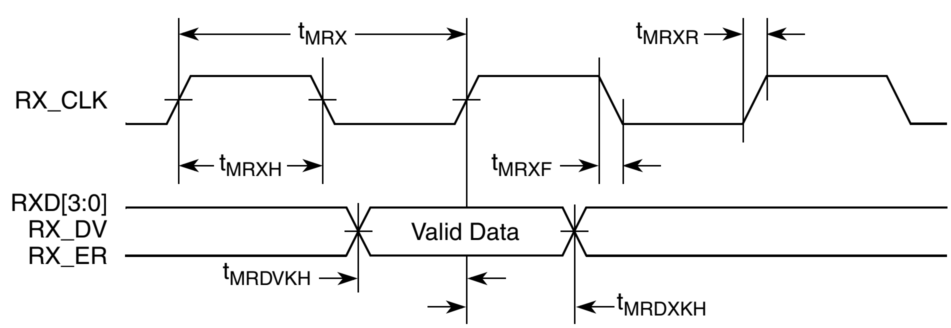


Figure 11. MII Receive AC Timing Diagram

8.2.2 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}	–0.5	—	0.5	ns
Data to clock input skew (at receiver)[2]	t_{SKRGT}	1.0	—	2.8	ns
Clock cycle duration[3]	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T[4, 5]	t_{RGTH}/t_{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX[3, 5]	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (80%–20%)	t_{RGTF}	—	—	0.75	ns

Notes:

1. In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).
2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.
5. Duty cycle reference is $LV_{DD}/2$.

Table 39. I^2C AC Electrical Specifications (continued)

Parameter	Symbol[1]	Min	Max	Unit
Fall time of both SDA and SCL signals[5]	t_{I2CF}	—	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Notes:
1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I^2C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I^2C timing (I2) for the time that the data with respect to the start condition (S) goes invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I^2C timing (I2) for the time that the data with respect to the stop condition (P) reaches the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} must be met only if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.
5.)The device does not follow the “I2C-BUS Specifications” version 2.1 regarding the t_{I2CF} AC parameter.

Figure 28 provides the AC test load for the I^2C.

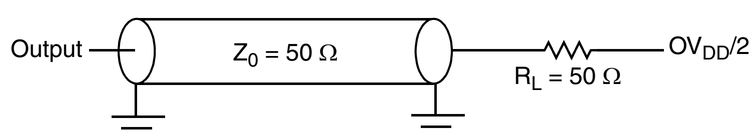


Figure 28. I^2C AC Test Load

Figure 29 shows the AC timing diagram for the I^2C bus.

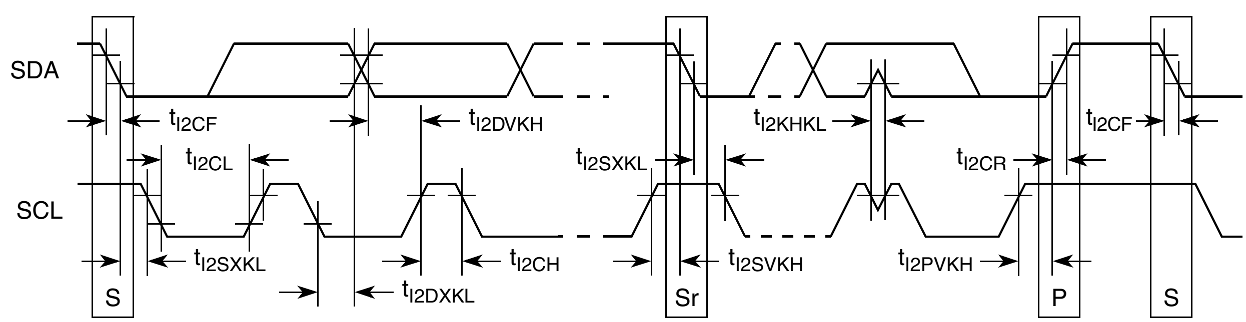


Figure 29. I^2C Bus AC Timing Diagram

14.2 Timer AC Timing Specifications

Table 44 provides the timer input and output AC timing specifications.

Table 44. Timers Input AC Timing Specifications[1]

Parameter	Symbol[2]	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:
1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 45 provides the DC electrical characteristics for the MPC8343EA GPIO.

Table 45. GPIO DC Electrical Characteristics

PArameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

15.2 GPIO AC Timing Specifications

Table 46 provides the GPIO input and output AC timing specifications.

Table 46. GPIO Input AC Timing Specifications[1]

Parameter	Symbol[2]	Min	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by external synchronous logic. GPIO inputs must be valid for at least t_{PIWID} ns to ensure proper operation.

18.3 Pinout Listings

Table 51 provides the pin-out listing for the MPC8343EA, 620-PBGA package.

Table 51. MPC8343EA (PBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI				
PCI1_INTA/IRQ_OUT	D20	O	OV_{DD}	2
PCI1_RESET_OUT	B21	O	OV_{DD}	—
PCI1_AD[31:0]	E19, D17, A16, A18, B17, B16, D16, B18, E17, E16, A15, C16, D15, D14, C14, A12, D12, B11, C11, E12, A10, C10, A9, E11, E10, B9, B8, D9, A8, C9, D8, C8	I/O	OV_{DD}	—
PCI1_C/BE[3:0]	A17, A14, A11, B10	I/O	OV_{DD}	—
PCI1_PAR	D13	I/O	OV_{DD}	—
PCI1_FRAME	B14	I/O	OV_{DD}	5
PCI1_TRDY	A13	I/O	OV_{DD}	5
PCI1_IRDY	E13	I/O	OV_{DD}	5
PCI1_STOP	C13	I/O	OV_{DD}	5
PCI1_DEVSEL	B13	I/O	OV_{DD}	5
PCI1_IDSEL	C17	I	OV_{DD}	—
PCI1_SERR	C12	I/O	OV_{DD}	5
PCI1_PERR	B12	I/O	OV_{DD}	5
PCI1_REQ[0]	A21	I/O	OV_{DD}	—
PCI1_REQ[1]/CPCI1_HS_ES	C19	I	OV_{DD}	—
PCI1_REQ[2:4]	C18, A19, E20	I	OV_{DD}	—
PCI1_GNT0	B20	I/O	OV_{DD}	—
PCI1_GNT1/CPCI1_HS_LED	C20	O	OV_{DD}	—
PCI1_GNT2/CPCI1_HS_ENUM	B19	O	OV_{DD}	—
PCI1_GNT[3:4]	A20, E18	O	OV_{DD}	—
M66EN	L26	I	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:31]	AC25, AD27, AD25, AH27, AE28, AD26, AD24, AF27, AF25, AF28, AH24, AG26, AE25, AG25, AH26, AH25, AG22, AH22, AE21, AD19, AE22, AF23, AE19, AG20, AG19, AD17, AE16, AF16, AF18, AG18, AH17, AH16	I/O	GV_{DD}	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LBCTL	H5	O	OV_{DD}	—
LALE	E3	O	OV_{DD}	—
LGPL0/LSDA10/cfg_reset_source0	F4	I/O	OV_{DD}	—
LGPL1/$\overline{\text{LSDWE}}$/cfg_reset_source1	D2	I/O	OV_{DD}	—
LGPL2/$\overline{\text{LSDRAS}}$/$\overline{\text{LOE}}$	C1	O	OV_{DD}	—
LGPL3/$\overline{\text{LSDCAS}}$/cfg_reset_source2	C2	I/O	OV_{DD}	—
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	C3	I/O	OV_{DD}	12
LGPL5/cfg_clkin_div	B3	I/O	OV_{DD}	—
LCKE	E4	O	OV_{DD}	—
LCLK[0:2]	D4, A3, C4	O	OV_{DD}	—
LSYNC_OUT	U3	O	OV_{DD}	—
LSYNC_IN	Y2	I	OV_{DD}	—
General Purpose I/O Timers				
GPIO1[0]/$\overline{\text{DMA\_DREQ0}}$/GTM1_TIN1/ GTM2_TIN2	D27	I/O	OV_{DD}	—
GPIO1[1]/$\overline{\text{DMA\_DACK0}}$/$\overline{\text{GTM1\_TGATE1}}$/ $\overline{\text{GTM2\_TGATE2}}$	E26	I/O	OV_{DD}	—
GPIO1[2]/$\overline{\text{DMA\_DDONE0}}$/ $\overline{\text{GTM1\_TOUT1}}$	D28	I/O	OV_{DD}	—
GPIO1[3]/$\overline{\text{DMA\_DREQ1}}$/GTM1_TIN2/ GTM2_TIN1	G25	I/O	OV_{DD}	—
GPIO1[4]/$\overline{\text{DMA\_DACK1}}$/ $\overline{\text{GTM1\_TGATE2}}$/$\overline{\text{GTM2\_TGATE1}}$	J24	I/O	OV_{DD}	—
GPIO1[5]/$\overline{\text{DMA\_DDONE1}}$/ $\overline{\text{GTM1\_TOUT2}}$/$\overline{\text{GTM2\_TOUT1}}$	F26	I/O	OV_{DD}	—
GPIO1[6]/$\overline{\text{DMA\_DREQ2}}$/GTM1_TIN3/ GTM2_TIN4	E27	I/O	OV_{DD}	—
GPIO1[7]/$\overline{\text{DMA\_DACK2}}$/$\overline{\text{GTM1\_TGATE3}}$/ $\overline{\text{GTM2\_TGATE4}}$	E28	I/O	OV_{DD}	—
GPIO1[8]/$\overline{\text{DMA\_DDONE2}}$/ $\overline{\text{GTM1\_TOUT3}}$	H25	I/O	OV_{DD}	—
GPIO1[9]/$\overline{\text{DMA\_DREQ3}}$/GTM1_TIN4/ GTM2_TIN3	F27	I/O	OV_{DD}	—
GPIO1[10]/$\overline{\text{DMA\_DACK3}}$/ $\overline{\text{GTM1\_TGATE4}}$/$\overline{\text{GTM2\_TGATE3}}$	K24	I/O	OV_{DD}	—
GPIO1[11]/$\overline{\text{DMA\_DDONE3}}$/ $\overline{\text{GTM1\_TOUT4}}$/$\overline{\text{GTM2\_TOUT3}}$	G26	I/O	OV_{DD}	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC1_RX_DV	U24	I	LV_{DD1}	—
TSEC1_RX_ER/GPIO2[26]	L28	I/O	OV_{DD}	—
TSEC1_RXD[3:0]	W26, W24, Y28, Y27	I	LV_{DD1}	—
TSEC1_TX_CLK	N25	I	OV_{DD}	—
TSEC1_TXD[3:0]	V28, V27, V26, W28	O	LV_{DD1}	10
TSEC1_TX_EN	W27	O	LV_{DD1}	—
TSEC1_TX_ER/GPIO2[31]	N24	I/O	OV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_COL/GPIO1[21]	P28	I/O	OV_{DD}	—
TSEC2_CRS/GPIO1[22]	AC28	I/O	LV_{DD2}	—
TSEC2_GTX_CLK	AC27	O	LV_{DD2}	—
TSEC2_RX_CLK	AB25	I	LV_{DD2}	—
TSEC2_RX_DV/GPIO1[23]	AC26	I/O	LV_{DD2}	—
TSEC2_RXD[3:0]/GPIO1[13:16]	AA25, AA26, AA27, AA28	I/O	LV_{DD2}	—
TSEC2_RX_ER/GPIO1[25]	R25	I/O	OV_{DD}	—
TSEC2_TXD[3:0]/GPIO1[17:20]	AB26, AB27, AA24, AB28	I/O	LV_{DD2}	—
TSEC2_TX_ER/GPIO1[24]	R27	I/O	OV_{DD}	—
TSEC2_TX_EN/GPIO1[12]	AD28	I/O	LV_{DD2}	3
TSEC2_TX_CLK/GPIO1[30]	R26	I/O	OV_{DD}	—
DUART				
UART_SOUT[1:2]/MSRCID[0:1]/ LSRCID[0:1]	B4, A4	O	OV_{DD}	—
UART_SIN[1:2]/MSRCID[2:3]/ LSRCID[2:3]	D5, C5	I/O	OV_{DD}	—
$\overline{\text{UART\_CTS}}$[1]/MSRCID4/LSRCID4	B5	I/O	OV_{DD}	—
$\overline{\text{UART\_CTS}}$[2]/MDVAL/LDVAL	A5	I/O	OV_{DD}	—
$\overline{\text{UART\_RTS}}$[1:2]	D6, C6	O	OV_{DD}	—
I^2C interface				
IIC1_SDA	E5	I/O	OV_{DD}	2
IIC1_SCL	A6	I/O	OV_{DD}	2
IIC2_SDA	B6	I/O	OV_{DD}	2
IIC2_SCL	E7	I/O	OV_{DD}	2

19 Clocking

Figure 37 shows the internal distribution of the clocks.

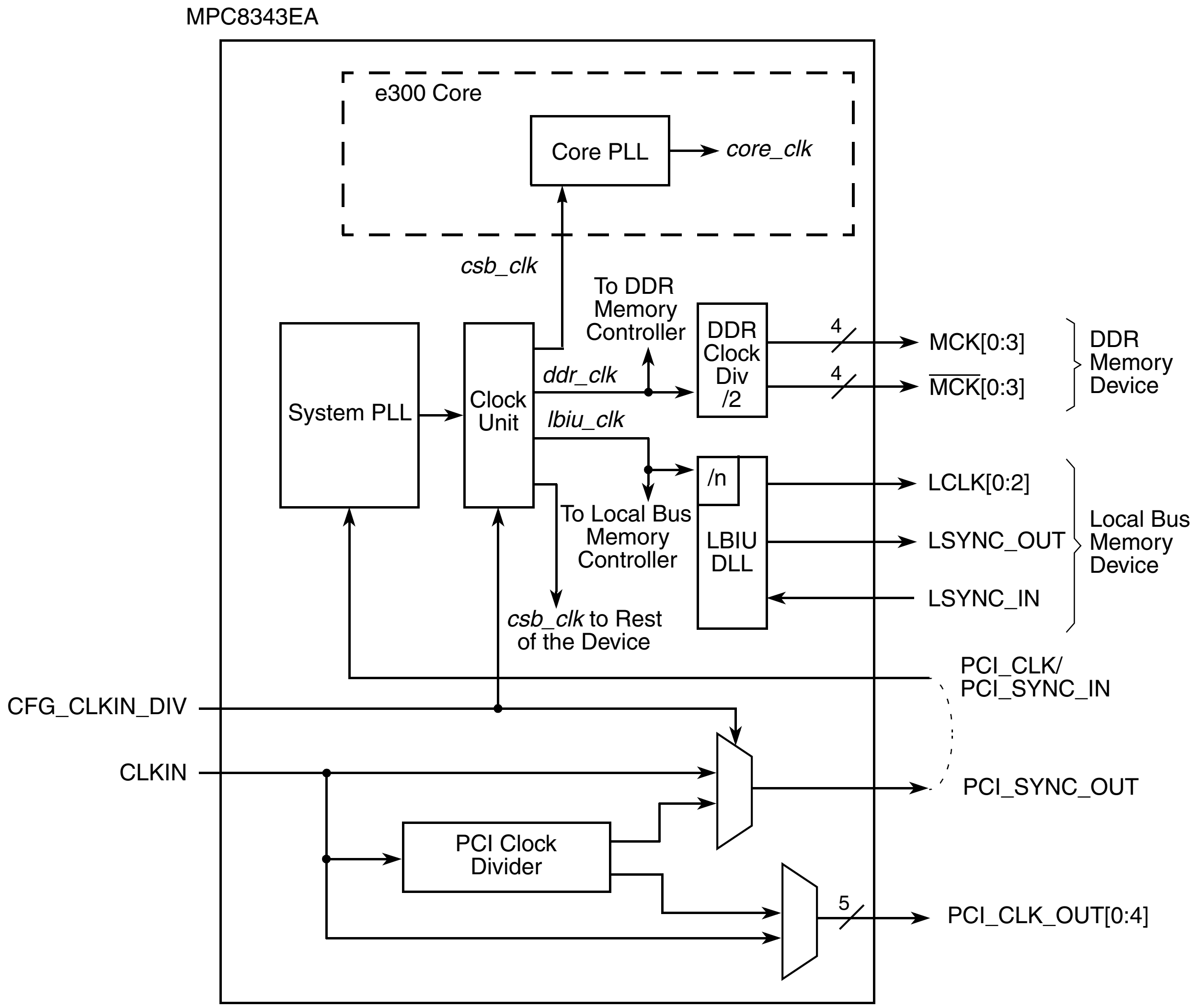


Figure 37. MPC8343EA Clock Subsystem

The primary clock source can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. When the MPC8343EA is configured as a PCI host device, CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (÷2) and the multiplexors for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCICD*n*] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUT*n* signals.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the MPC8343EA to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock and the CLKIN signal should be tied to GND.

Table 53 provides the operating frequencies for the MPC8343EA PBGA under recommended operating conditions.

Table 53. Operating Frequencies for PBGA

Parameter[1]	266 MHz	333 MHz	400 MHz	Unit
e300 core frequency (*core_clk*)	200–266	200–333	200–400	MHz
Coherent system bus frequency (*csb_clk*)	100–266			MHz
DDR1 memory bus frequency (MCK)[2]	100–133			MHz
DDR2 memory bus frequency (MCK)[3]	100–133			MHz
Local bus frequency (LCLK*n*)[4]	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66			MHz
Security core maximum internal operating frequency	133			MHz
USB_DR, USB_MPH maximum internal operating frequency	133			MHz

1 The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

2 The DDR data rate is 2× the DDR memory bus frequency.

3 The DDR data rate is 2× the DDR memory bus frequency.

4 The local bus frequency is ½, ¼, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBIUCM]).

19.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 54 shows the multiplication factor encodings for the system PLL.

Table 54. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10

Table 54. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

As described in Section 19, "Clocking," the LBIUCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 55 and Table 56 show the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 55. CSB Frequency Options for Host Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J – T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

20.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 60 shows heat sink thermal resistance for PBGA of the MPC8343EA.

Table 60. Heat Sink and Thermal Resistance of MPC8343EA (PBGA)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	13.5
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	9.6
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	8.8
AAVID 31 × 35 × 23 mm pin fin	Natural convection	11.3
AAVID 31 × 35 × 23 mm pin fin	1 m/s	8.1
AAVID 31 × 35 × 23 mm pin fin	2 m/s	7.5
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	9.1
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	7.1
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	6.5
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	10.1

$OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N) \div 2$.

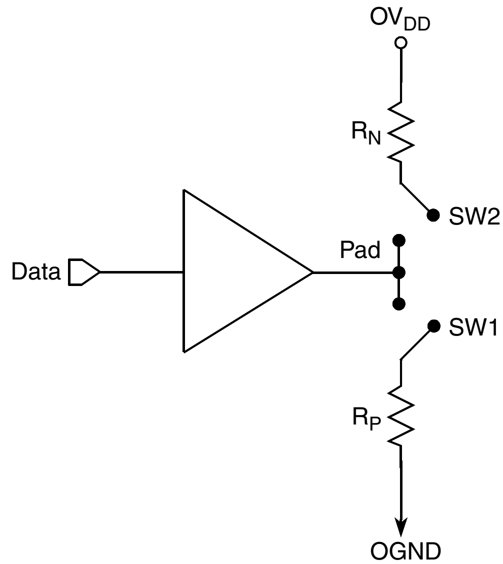


Figure 39. Driver Impedance Measurement

Two measurements give the value of this resistance and the strength of the driver current source. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = (1 \div (1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1 \div V_2 - 1)$. The drive current is then $I_{source} = V_1 \div R_{source}$.

Table 61 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 61. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI Signals (Not Including PCI Output Clocks)	PCI Output Clocks (Including PCI_SYNC_OUT)	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	42 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	42 Target	20 Target	Z_0	W
Differential	NA	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

21.6 Configuration Pin Multiplexing

The MPC8343EA power-on configuration options can be set through external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see the customer-visible configuration pins). These pins are used as output only pins in normal operation.